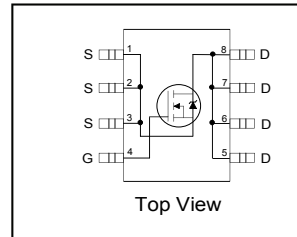


**HEXFET® Chip-Set for DC-DC Converters**

- N Channel Application Specific MOSFETs
- Ideal for Mobile DC-DC Converters
- Low Conduction Losses
- Low Switching Losses
- Lead-Free


**Description**

This new device employs advanced HEXFET Power MOSFET technology to achieve an unprecedented balance of on-resistance and gate charge. The reduced conduction and switching losses make this device ideal for high efficiency DC-DC Converters that power the latest generation of mobile microprocessors.

The IRF7805PbF offers maximum efficiency for mobile CPU core DC-DC converters.

**Devices Features**

	<b>IRF7805PbF</b>
<b>V<sub>DS</sub></b>	<b>30V</b>
<b>R<sub>DS(on)</sub></b>	<b>11mΩ</b>
<b>Q<sub>g</sub></b>	<b>31nC</b>
<b>Q<sub>sw</sub></b>	<b>11.5nC</b>
<b>Q<sub>oss</sub></b>	<b>36nC</b>

<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7805PbF	SO-8	Tape and Reel	4000	IRF7805PbF

Symbol	Parameter	Max.	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-to-Source Voltage	± 12	
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V ③	13	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V ③	10	
I <sub>DM</sub>	Pulsed Drain Current ①	100	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Maximum Power Dissipation ③	2.5	W
P <sub>D</sub> @ T <sub>A</sub> = 70°C	Maximum Power Dissipation ③	1.6	
	Linear Derating Factor	0.02	W/°C
T <sub>J</sub> T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to + 150	°C

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJL</sub>	Junction-to-Drain Lead ⑤	—	20	°C/W
R <sub>θJA</sub>	Junction-to-Ambient ③	—	50	

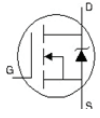
**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage ⑥	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance ⑥	—	9.2	11	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7.0A ②
V <sub>GS(th)</sub>	Gate Threshold Voltage ⑥	1.0	—	3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	70	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
		—	—	10		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
		—	—	150		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 100°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 12V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -12V

**Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

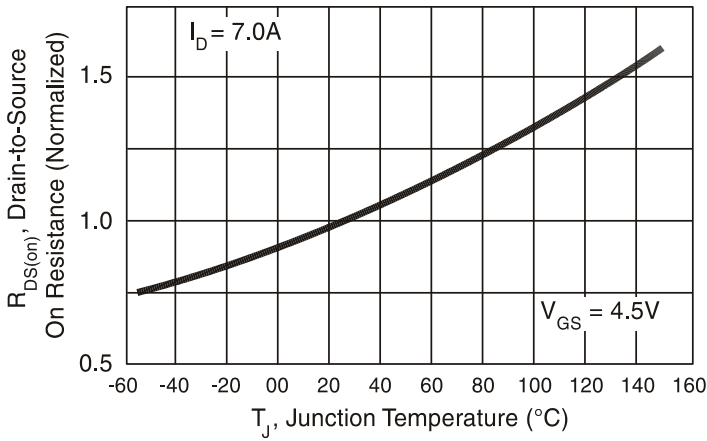
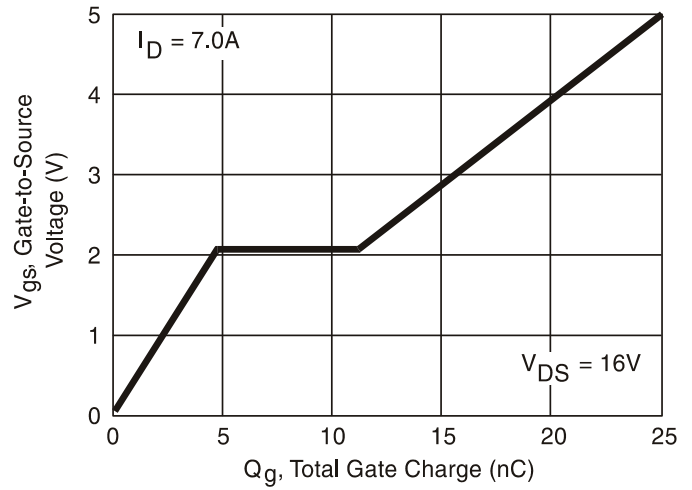
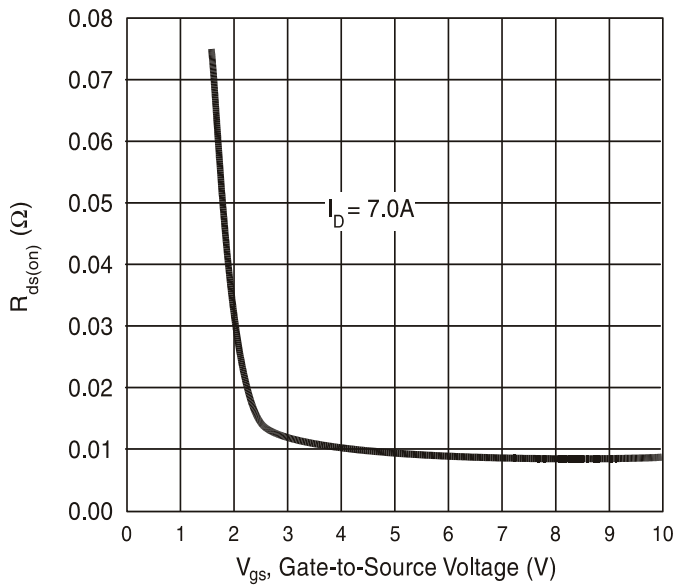
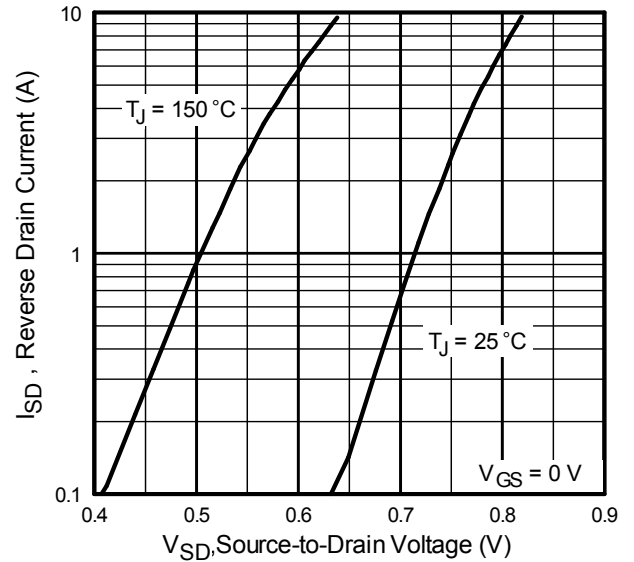
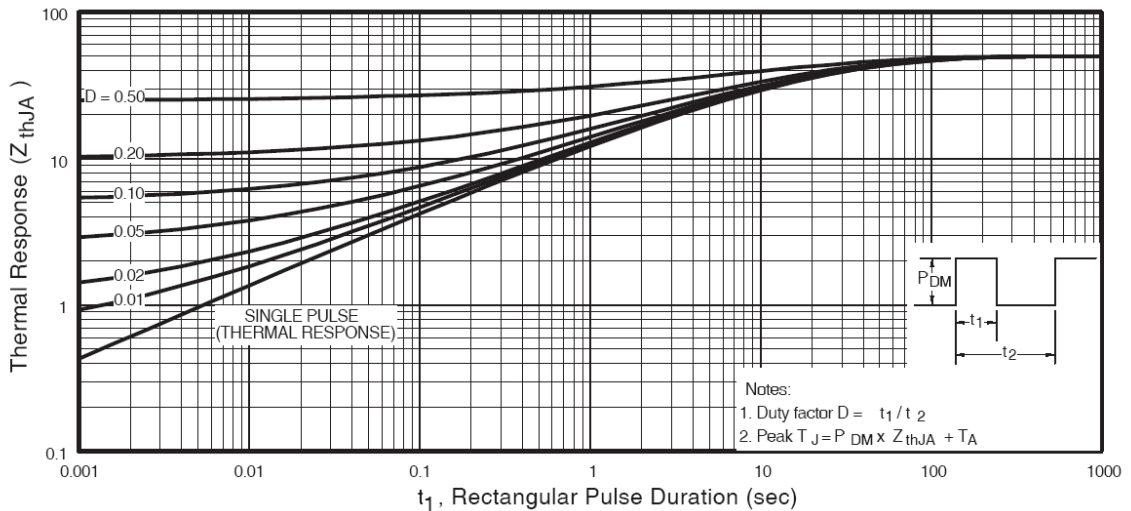
Q <sub>g</sub>	Total Gate Charge ⑥	—	22	31	nC	V <sub>GS</sub> = 5.0V V <sub>DS</sub> = 16V I <sub>D</sub> = 7.0A
Q <sub>gs1</sub>	Pre -V <sub>th</sub> Gate-to-Source Charge	—	3.7	—		
Q <sub>gs2</sub>	Post-V <sub>th</sub> Gate-to-Source Charge	—	1.4	—		
Q <sub>gd</sub>	Gate-to-Drain Charge	—	6.8	—		
Q <sub>sw</sub>	Switch Charge (Q <sub>gs2</sub> + Q <sub>gd</sub> ) ⑥	—	8.2	11.5		
Q <sub>oss</sub>	Output Charge ⑥	—	30	36	nC	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
R <sub>G</sub>	Gate Resistance	0.5	—	1.7	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	16	—	ns	V <sub>DD</sub> = 16V, V <sub>GS</sub> = 4.5V ② I <sub>D</sub> = 7.0A R <sub>G</sub> = 2Ω Resistive Load
t <sub>r</sub>	Rise Time	—	20	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	38	—		
t <sub>f</sub>	Fall Time	—	16	—		

**Diode Characteristics**

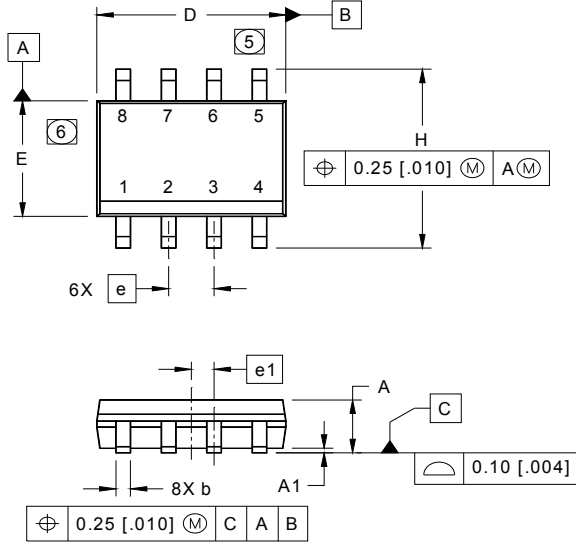
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)①	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode)	—	—	106		
V <sub>SD</sub>	Diode Forward Voltage⑥	—	—	1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 7.0A, V <sub>GS</sub> = 0V
Q <sub>rr</sub>	Reverse Recovery Charge ④	—	88	—	nC	di/dt = 700A/μs V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, I <sub>S</sub> = 7.0A
Q <sub>rr</sub>	Reverse Recovery Charge ④	—	55	—		di/dt = 700A/μs (with 10BQ040) V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, I <sub>S</sub> = 7.0A

**Notes:**

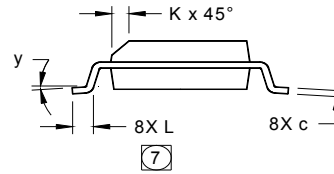
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ③ When mounted on 1" in square copper board, t < 10 sec.
- ④ Typ = measured - Q<sub>oss</sub>
- ⑤ R<sub>θ</sub> is measured at T<sub>J</sub> of approximately 90°C.
- ⑥ Devices are 100% tested to these parameters.


**Fig. 1** Normalized On-Resistance vs. Temperature

**Fig. 2** Typical Gate Charge vs. Gate-to-Source Voltage

**Fig. 3** Typical  $R_{DS(on)}$  vs. Gate-to-Source Voltage

**Fig. 4** Typical Source-Drain Diode Forward Voltage

**Fig. 5.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

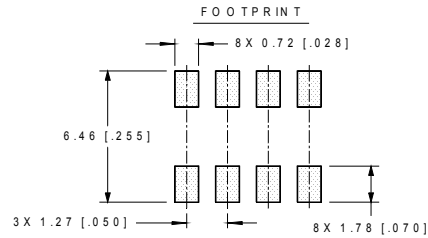
## SO-8 Package Outline (Dimensions are shown in millimeters (inches))



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

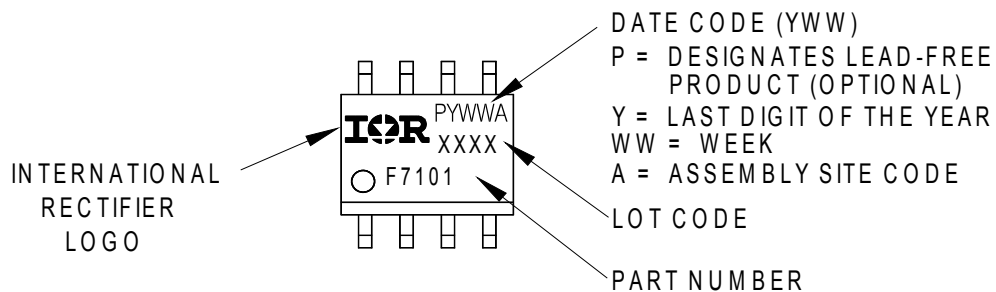


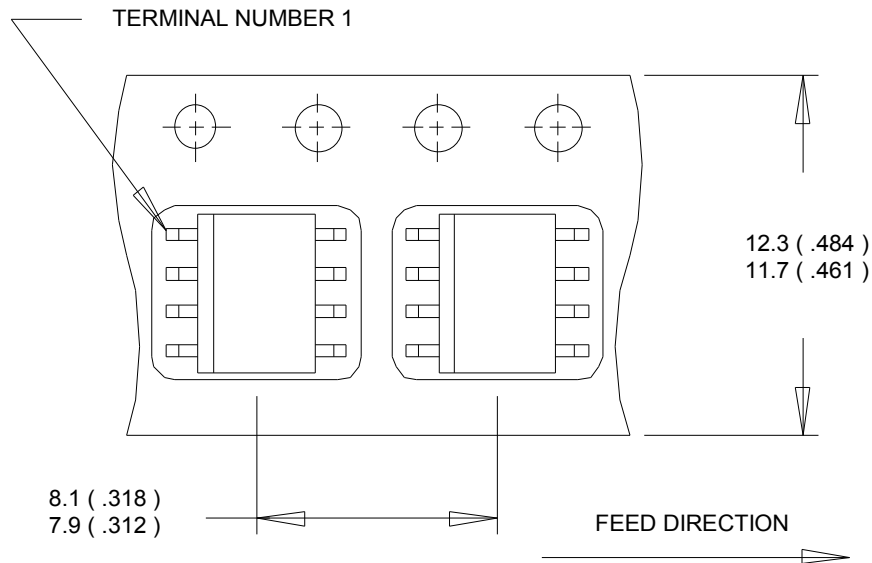
- NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
  2. CONTROLLING DIMENSION: MILLIMETER
  3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
  5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
  6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
  7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



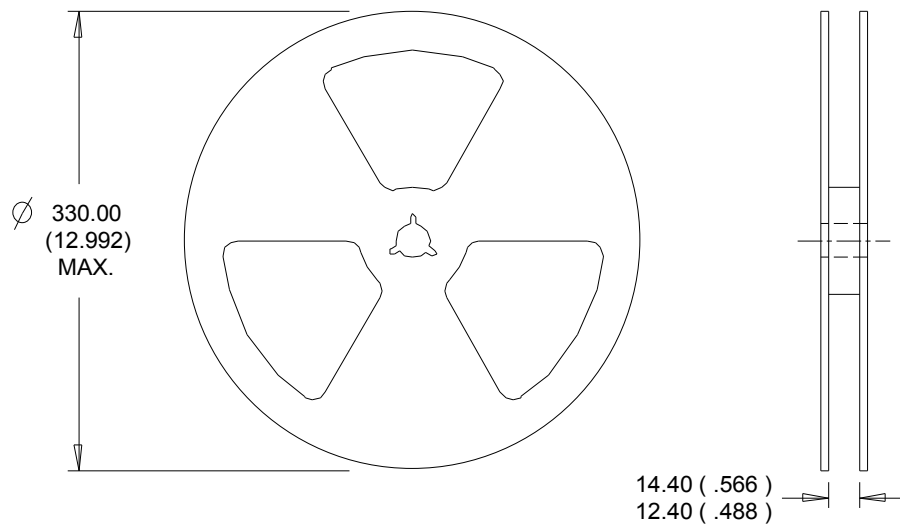
## SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



**SO-8 Tape and Reel** (Dimensions are shown in millimeters (inches))

**NOTES:**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.


**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

**Qualification Information**

<b>Qualification Level</b>	Consumer	
<b>Moisture Sensitivity Level</b>	SO-8	MSL1 (per JEDEC J-STD-020D) <sup>†</sup>
<b>RoHS Compliant</b>	Yes	

<sup>†</sup> Applicable version of JEDEC standard at the time of product release.

**Revision History**

Date	Comments
08/23/2016	<ul style="list-style-type: none"> <li>Changed datasheet with Infineon logo - all pages.</li> <li>Corrected typo Qoss from typ/max "3.0nC/3.6nC" to "30nC/36nC" on page 2.</li> <li>Added disclaimer on last page.</li> </ul>

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